

## EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	1	"10567250"	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/04/30 14:01
S2	572	257/30.ccls.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/04/30 15:28
S3	6	(micro near2 tunnel near2 junction near2 circuit)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/04/30 15:45
S4	94	(tunnel near2 junction near2 circuit)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/04/30 15:45
S5	484975	(riken or (nec near2 (corp or corporation)))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/06/23 16:29
S6	466	(michio near2 watanabe) or (yasunobu near2 nakamura)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/06/23 16:31
S7	8	S6 and (tunnel near2 junction)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/06/23 16:31
S8	254	S5 and (tunnel near2 junction)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/06/23 16:33
S9	117	(single near2 electron near2 transistor) and (josephson)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/23 19:01

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S10	466	(michio near2 watanabe) or (yasunobu near2 nakamura)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/06/23 19:10
S11	29970	(single near2 electron near2 transistor) or (josephson) or (quantum near2 (device or memory or diode or transistor)) or (tunneling near2 (device or memory or diode or transistor))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/23 19:15
S12	5	S10 and S11	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/23 19:15
S13	6466	(josephson) near2 (junction or device)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/24 09:45
S14	300	S13 and "438".clas.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/24 09:45
S15	118	S14 and (nb or niobium)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/24 09:48
S16	36443	(single near2 electron near2 transistor) or (josephson) or (quantum near2 (device or memory or diode or transistor)) or (tunneling near2 (device or memory or diode or transistor)) or SQUID or (superconducting near2 quantum near2 interference near2 device) or (SNS near3 (tunnel or junction))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/25 14:36
S17	1897	S16 and ((through near2 hole))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/25 14:37
S18	1047536	((through near2 hole))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/25 14:37

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S19	202637	(niobium or nb)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/25 14:38
S20	276	S17 and S19	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/25 14:38
S21	1773	S16 and (recession or recess or recessed or trench) and (hole or (through near2 hole))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/25 14:44
S22	159	S19 and S21	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/25 14:45
S23	1	"7550759"	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/25 15:43
S24	5	("20020188578"   "20030207766"   "20040012407"   "6353330"   "6605822"). PN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/06/25 15:45
S25	11	("20020188578"   "20030207766"   "20040012407"   "6353330"   "6605822"). PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/25 15:45
S26	117	(single near2 electron near2 transistor) and (josephson)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/25 15:55
S27	109	(single near2 electron near2 transistor) and (josephson near2 junction)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/25 15:55
S28	79	(single near2 electron near2 transistor) and (two with (josephson near2 junction))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/25 15:55

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S30	233025	(niobium or nb)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/25 16:45
S33	144	S29 and S30 and hole	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/25 16:46
S35	233025	(niobium or nb)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/25 16:47
S36	750	257/31.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/25 16:48
S37	217	S35 and S36	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/25 16:48
S38	37	S37 and hole	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT	OR	ON	2009/06/25 16:48
S39	467	(michio near2 watanabe) or (yasunobu near2 nakamura)	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/09/28 16:58
S40	0	Y01N4/00\$	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/09/29 12:50
S41	3612	H01L39/22\$1	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/09/29 12:50

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S42	14233		H01L29/76\$1	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/09/29 12:51
S43	5	S41 and (recession or recess or recessed or trench) and (hole or (through near2 hole))		US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/09/29 12:52
S44	37180	(single near2 electron near2 transistor) or (josephson) or (quantum near2 (device or memory or diode or transistor)) or (tunneling near2 (device or memory or diode or transistor)) or SQUID or (superconducting near2 quantum near2 interference near2 device) or (SNS near3 (tunnel or junction))		US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/09/29 12:53
S45	1821	S44 and (recession or recess or recessed or trench) and (hole or (through near2 hole))		US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/09/29 12:54
S46	239	S44 and (recession or recess or recessed or trench) and (hole or (through near2 hole)) and (FIB or (ion near beam))		US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/09/29 12:54
S47	26	("20030058799"   "20030187237"   "20040219596"   "20040229386"   "20050006224"   "20050007002"   "20050009039"   "20050164001"   "20050164211"   "20050241933"   "20050271807"   "20060006377"   "5795782"   "5798042"   "5888591"   "5893974"   "6015714"   "6413792"   "6464842"   "6555362"   "6627067"   "6783643"   "6958216"   "7001792"   "7005264"   "7189503").PN. OR ("7468271").URPN.		US-PGPUB; USPAT; USOCR	OR	ON	2009/09/29 12:59
S48	29648	(single near2 electron near2 transistor) or (josephson and tunnel) or (quantum near2 (device or memory or diode or transistor)) or (tunneling near2 (device or memory or diode or transistor)) or SQUID or (superconducting near2 quantum near2 interference near2 device) or (SNS near3 (tunnel or junction))		US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/09/29 13:06
S49	1711	S48 and (recession or recess or recessed or trench) and (hole or (through near2 hole))		US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/09/29 13:06

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S50	233	S48 and (recession or recess or recessed or trench) and (hole or (through near2 hole)) and (FIB or (ion near beam))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/09/29 13:07
S51	580	257/30.ccls.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	OFF	2009/09/29 13:41
S52	3	S51 and (recession or recess or recessed or trench) and (hole or (through near2 hole)) and (FIB or (ion near beam))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/09/29 13:41
S53	414	438/594.ccls.	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/09/29 13:42
S54	0	S53 and (recession or recess or recessed or trench) and (hole or (through near2 hole)) and (FIB or (ion near beam))	US-PGPUB; USPAT; FPRS; EPO; JPO; DERWENT	OR	ON	2009/09/29 13:42
S55	7	("6139713"   "6214738").PN. OR ("6737668").URPN.	US-PGPUB; USPAT; USOCR	OR	ON	2009/09/29 17:05